



VS-FB180SA10P Information

Heisener.com

VS-FB180SA10P Part Number

Manufacturer Vishay Semiconductor Diodes Division

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 180A SOT-227

SOT-227-4 **Package**

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only

E-mail: salesdept@heisener.com



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Certified Quality

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VS-FB180SA10P Specifications

Manufacturer Part Number VS-FB180SA10P Manufacturer Vishay Semiconductor Diodes Division Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package SOT-227-4 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 180A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 380nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 10700pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 480W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 180A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227 Package / Case SOT-227-4		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C180ADrive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs380nC @ 10VInput Capacitance (Ciss) (Max) @ Vds10700pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 180A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227Package / CaseSOT-227-4	Package	SOT-227-4
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 180A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 10700pF @ 25V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 100V MOSFET (Metal Oxide) 100V 100V 100V 100V 100V 100V 100V 100V 4V @ 250µA 4V @ 250µA 10700pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Series	-
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C180ADrive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs380nC @ 10VInput Capacitance (Ciss) (Max) @ Vds10700pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 180A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227Package / CaseSOT-227-4	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C180ADrive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs380nC @ 10VInput Capacitance (Ciss) (Max) @ Vds10700pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 180A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227Package / CaseSOT-227-4	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs380nC @ 10VInput Capacitance (Ciss) (Max) @ Vds10700pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 180A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227Package / CaseSOT-227-4	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature Chassis Mount Supplier Device Package Package / Case 4V @ 250μA 380nC @ 10V 10700pF @ 25V +20V +20V FET Feature - - Chassis Mount SOT-227-4	Current - Continuous Drain (Id) @ 25°C	180A
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 180A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227 Package / Case	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 180A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227 Package / Case SOT-227-4	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)480W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 180A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227Package / CaseSOT-227-4	Gate Charge (Qg) (Max) @ Vgs	380nC @ 10V
FET Feature - Power Dissipation (Max) 480W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 180A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227 Package / Case SOT-227-4	Input Capacitance (Ciss) (Max) @ Vds	10700pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 180A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227 Package / Case SOT-227-4	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs6.5 mOhm @ 180A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227Package / CaseSOT-227-4	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227 Package / Case SOT-227-4	Power Dissipation (Max)	480W (Tc)
Mounting Type Chassis Mount Supplier Device Package SOT-227 Package / Case SOT-227-4	Rds On (Max) @ Id, Vgs	6.5 mOhm @ 180A, 10V
Supplier Device Package SOT-227 Package / Case SOT-227-4	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case SOT-227-4	Mounting Type	Chassis Mount
	Supplier Device Package	SOT-227
Report errors?	Package / Case	SOT-227-4
		Report errors?

VS-FB180SA10P Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

VS-FB180SA10P Payment Methods



















VS-FB180SA10P Shipping Methods













If you have any question about VS-FB180SA10P, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com